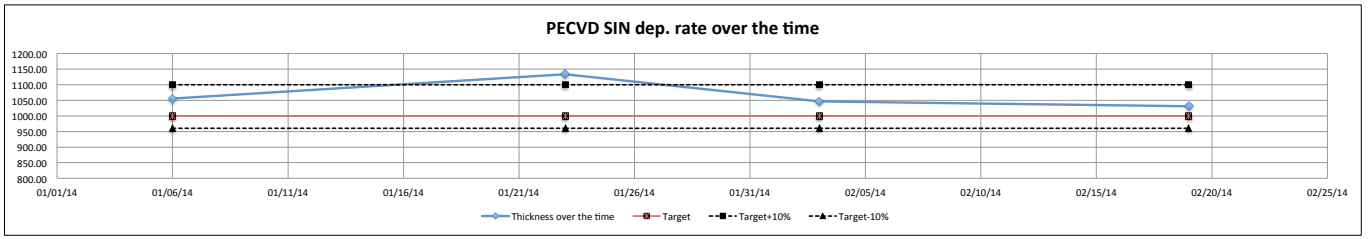
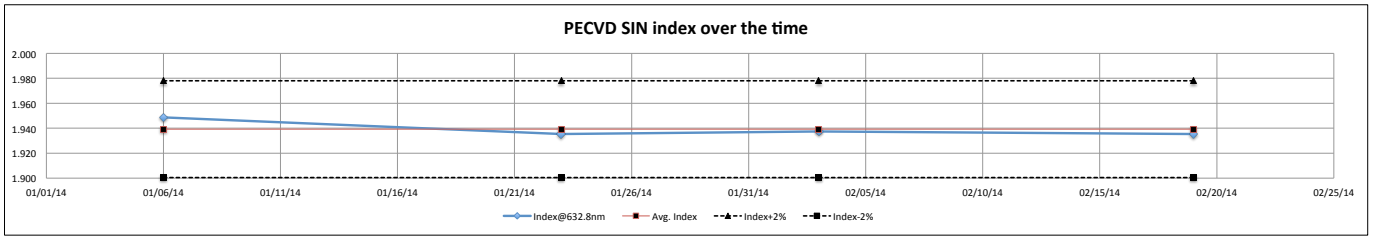
Date	User	Material	Recipe	Substrate T	Measured Thickness	Target Th.	Target+10%	Target-10%	AVG Thick.	AVG+10%	AVG-10%	Dep.time	Dep.time	JAW EC-400 (Woolam Spectroscopic		AVG index	AVG+2%	AVG-2%	Dep.rate	Stress	HF etch rate wafer	LPD (light point defects)		AVG dep.rate	AVG+10%	AVG-10%	Additional Notes
1/1/2012	User	SiN	SiN_10	250 C	(Å)	1000A	1100A	900A	1022A			min/sec	sec	Index @632.8nm	Index@1550nm				(nm/min)	Tensile (+456MPa)	(nm/min)	before dep.	after dep.				
01/06/14	Biljana	SiN	SiN_10	250	1055.81	1000.00	1100.00	900.00	1066.62	1173.28	959.96	9'28.1"	568.1	1.949	1.903	1.939	1.978	1.900	11.15	571.87		78	547	11.27	12.39	10.14	4" Si wafer
01/23/14	Biljana	SiN	SiN_10	250	1133.40	1000.00	1100.00	900.00	1066.62	1173.28	959.96	9'28.1"	568.1	1.935	1.890	1.939	1.978	1.900	11.97	446.88	90.66	137	377	11.27	12.39	10.14	4" Si wafer, very nice, uniform film
02/03/14	Biljana	SiN	SiN_10	250	1046.60	1000.00	1100.00	900.00	1066.62	1173.28	959.96	9'28.1"	568.1	1.937	1.893	1.939	1.978	1.900	11.05	486.75	81.21	322	604	11.27	12.39	10.14	4" Si wafer, very nice, uniform film
02/19/14	Biljana	SiN	SiN_10	250	1030.66	1000.00	1100.00	900.00	1066.62	1173.28	959.96	9'28.1"	568.1	1.935	1.890	1.939	1.978	1.900	10.89	353.92	77.32	75	323	11.27	12.39	10.14	4" Si wafer, very nice, uniform film

Target Thickness	1000.00
Target+10%	1100.00
Target-10%	900.00
Avg Thickness	1066.62
Avg +10%	1173.28
Avg - 10%	959.96

Avg index@632.8	1.939
Avg+2%	1.978
Avg-2%	1.900

Avg. Rate	11.27
Avg +10%	12.39
Avg - 10%	10.14